

CURRICULUM VITAE

Name: PANAGIOTA
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CURRENT OCCUPATION

2003- June 2012, Application Professor, Department of Science, Technological Education Institute of Kavala.

June 2012 – to present, Assistant Professor, Department of Science, Technological Education Institute of Kavala.

COURSES

1. Physics Laboratory.
2. Electromagnetic Theory.
3. Electronics I Laboratory.
4. Microprocessor – Microcomputers (Lectures and Laboratory)

EDUCATION - DEGREES

1. **1993, BSc** in Physics from the Aristotle University of Thessaloniki, Greece.
2. **1996, MSc** in Electronic Physics (Radioelectrology) from the Aristotle University of Thessaloniki Department of Physics, Greece.
3. **2002, Ph.D.** degree in Microelectronic from Democritus University of Thrace, Department of Electrical Engineering, Xanthi, Greece.

THESIS - LIST OF PUBLICATIONS

1. THESIS

- 1.1. **2002, «Design, Fabrication, Characterization and Simulation of silicon p⁺np Bulk - Barrier diodes», Ph. D. thesis, Laboratory of Electrical and Electronic Materials Technology, Department of Electrical and Computer Engineering, Democritus University of Thrace, Xanthi, Greece.**

2. PAPERS

- 2.1. **P. Papadopoulou, N. Georgoulas, L. Georgopoulos, A. Thanailakis, «A model for the dc electrical behavior of Bulk-Barrier Diodes», Electrical Engineer, Archiv fur Elektrotechnik, Vol. 83 (4), pp. 203-211 (2001).**
- 2.2. **P. Papadopoulou, N. Georgoulas and A. Thanailakis, «Simulation and Experimental Results on the Switching Behaviour of Bulk-Barrier Diodes», Microelectronics Journal, Vol. 33 (5-6), pp. 487-494 (2002).**
- 2.3. **P. Papadopoulou, N. Georgoulas and A. Thanailakis, «An extensive study of the photocurrent amplification mechanism of silicon Bulk - Barrier diodes based on simulation and experimental results», Thin Solid Film, Vol. 415, pp. 276-284 (2002).**
- 2.4. **P. Papadopoulou, N. Georgoulas , L. Magafas, «A study of the optical response speed of silicon Bulk -Barrier photodiodes based on simulation results», Optoelectronics and Advanced materials - Rapid Communications Vol. 1, No. 8, p. 379 - 384 (2007).**
- 2.5. **P. Papadopoulou, Ant. Meletis, G. Doukakis, C. Mertzaniadis, «Frequency Domain Response of Dielectrics for TE Plane Waves», European Journal of Scientific Research, Vol. 34, No.4, pp.463-473 (2009).**
- 2.6. **P. Papadopoulou, L. Georgopoulos «A study of the silicon Bulk-Barrier Diodes designed in planar technology by means of simulation» Journal of Engineering Science and Technology Review, Vol. 2, pp. 157-164, (2009).**
- 2.7. **M.Hanias, L.Magafas, S.Stavrinides, P.Papadopoulou and M.Ozer, «Chaotic behavior of the forward I-V characteristic of the Al/a-SiC:H/c-**

Si(n) heterojunction Complexity», Proceedings of the 4th International Interdisciplinary Chaos Symposium, p.221,(2013), Chaos and Complex Systems 2013, pp 475-479.

3. CONFERENCES

- 3.1. **P. Papadopoulou, L. Georgopoulos, N. Georgoulas, A. Thanailakis, «Stimulation of Electrical and Optical behaviour of Bulk-Barrier diodes**», XIII Greek Solid State Physics Conference, Thessaloniki 22-24 September 1997.
- 3.2. **P. Papadopoulou, N. Georgoulas, A. Thanailakis, «Transient analysis of Bulk-Barrier diodes using simulation**», XIV Greek Solid State Physics Conference, Ioannina 15-18 September 1998.
- 3.3. **P. Papadopoulou, N. Georgoulas, A. Thanailakis, «Study of the switching behaviour of silicon Bulk-Barrier photodiodes in light pulse using simulation**», XV Greek Solid State Physics Conference, Patra 27-29 September 1999.
- 3.4. **P. Papadopoulou, N. Georgoulas, A. Thanailakis, «Influence of the light modulation frequency on the external quantum efficiency of silicon p⁺np photodiodes**», XVII Greek Solid State Physics Conference, Xanthi 6-9 September 2001.
- 3.5. **P. Papadopoulou, L. Georgopoulos, N. Georgoulas, «Study of the influence of the incident light power on the optoelectronic behaviour of silicon p⁺np photodiodes**», XXI Greek Solid State Physics Conference, Nicosia Cyprus, 28-31 August 2005.

REFERENCES

2.1

1. **P. Papadopoulou, et al.**, *Microelectronics Journal*, Vol. 33 (5-6), pp. 487-494 (2002).
2. **P. Papadopoulou, et al.**, *Thin Solid Film*, Vol. 415, pp. 276-284 (2002).
3. **C. M. Sun et al.**, *Nuclear Instruments & Methods in Physics Research A*, Vol. 547, pp. 437 - 449 (2005).

2.2

1. **Der-Feng Guo**, *IEEE Electron Device Letters*, Vol. 24, No3, pp. 162 - 164, (2003).
2. **Der-Feng Guo, et al.**, *IEEE Transactions on Electron Devices*, Vol.51, No. 4, pp. 542 - 547, (2004).
3. **Jing-Yuh Chen**, «Investigation of InP- based Heterojunction Bipolar Transistors and Optoelectronic Switching Devices», Ph.D. Thesis Institute of Microelectronics, Department of Electrical Engineering, National Cheng Kung University Tainan, Taiwan (2005).
4. **Der-Feng Guo**, *Optoelectronics, IEE Proceedings*, Vol.153, No.2, pp.63 -66, (2006).
5. **Weng, T.-Y., et al.**, *Conference on Optoelectronic and Microelectronic Materials and Devices, Proceedings, COMMAD*, Article No. 4429888, pp. 94-97, (2006).
6. **Der-Feng Guo**, *Journal of the Electrochemical Society*, Vol.154, No.1, pp. H13 - H15, (2007).
7. **Der-Feng Guo, et al.**, *Surface Review and Letters*, Vol.15, Issue 1-2, pp 139-144, (2008).
8. **Chih-Hung Yen**, «Investigation of AlGaInP-based Light-Emitting Diodes and GaAs-based Optoelectronic Switching Devices», Ph.D. Thesis Institute of Microelectronics, Department of Electrical Engineering, National Cheng Kung University Tainan, Taiwan (2009).
9. **Der-Feng Guo**, *ECS Transactions* 28 (4), pp. 111-118 (2010).

2.3

1. **C. M. Sun et al.**, *Nuclear Instruments & Methods in Physics Research A*, Vol. 547, pp. 437 - 449 (2005).

2. «Infrared HgCdTe Optical Detectors» Book Chapter, Book Title «Optoelectronic Devices Advance Simulation and Analysis», Springer New York, pp. 381-403 (2005).

3. Zhou Quan et al., Journal of Semiconductors, Vo. 34, No. 7, pp. 074010-1-4 (2013).

2.4

1. **P. Papadopoulou, L. Georgopoulos**, Journal of Engineering Science and Technology Review, Vol. 2, pp. 157-164, (2009).

2.6

1. **V. Janardhanam, Yeon-Ho Kil, Kyu-Hwan Shim, V. Rajagopal Reddy and Chel-Jong Choi**, Materials Transactions, Vol.54 No.07 (2013) pp.1067-1072 .

RESEARCH PROJECTS

1. **September 2008-2009**, Scientific Person in charge, *Project name*: «Silicon Bulk-Barrier Diodes designed in planar technology». Research work supported by the Research and Fund Administration Committee of Technological Education Institute of Kavala.

2. **September 2003**, Scientific Person in charge of the Department of Science of T.E.I. Kavala's, *Project name*: «Additional educational equipment of departments in higher education».

3. **1 -7 - 1999 to 29- 6 - 2001**, *Project name*: «Improvement of infrastructure of the Laboratory of Electrical and Electronic Materials Technology, of the Department of Electrical and Computer Engineering of Democritus University of Thrace». Research work supported by the Research and Fund Administration Committee of Democritus University of Thrace.

4. **May 1, 1998 - April 30, 1999**, *Project name*: «Design, fabrication, study and optimization of silicon photo diode with high quantum efficiency to the blue spectra of visible light». Research work supported by the Greek General Secretariat of Research and Technology. *Contractor*: DEMOCRITUS University of Thrace, Department of Electrical and Computer Engineering.

5. **1 -3 - 1997 to 31- 12 - 1997**, *Project name:* «Low power design. High level power consumption of digital processing». Research work supported by the Research and Fund Administration Committee of Democritus University of Thrace.

6. **13 - 6 - 1996 to 12- 10 - 1996**, *Project name:* «Growth, modelling and simulation of SiO₂ thin films with the technique of thermal oxidation». Research work supported by the Research and Fund Administration Committee of Democritus University of Thrace.

LANGUAGES

- English